

# Belle II DEPFET pixel detector



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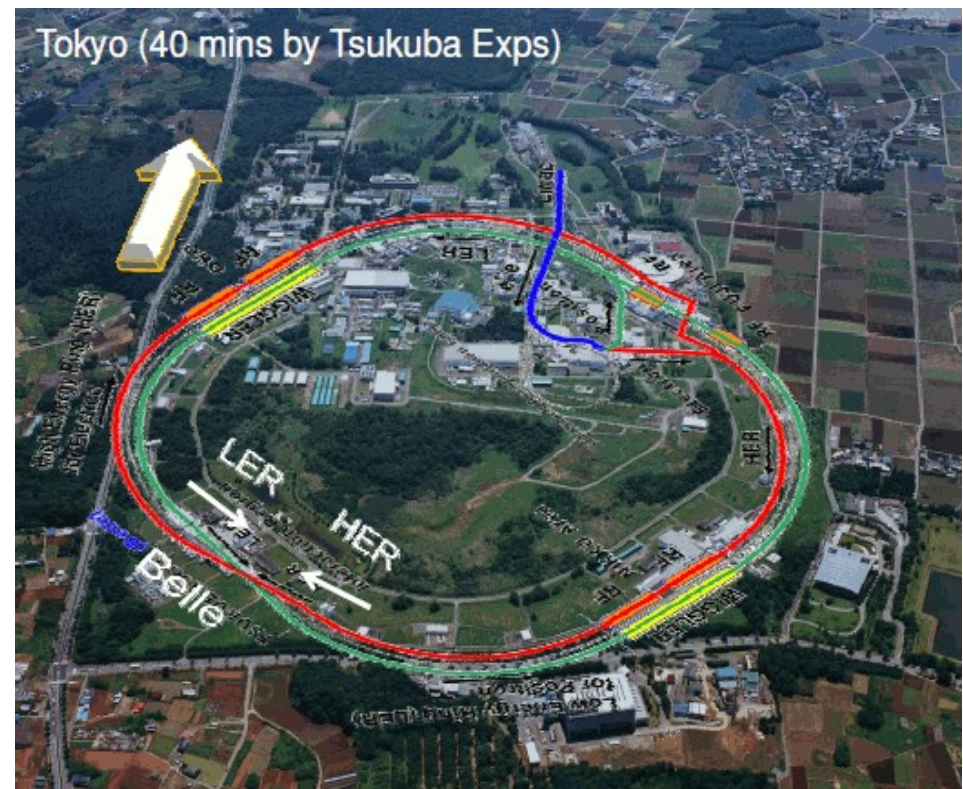
for the DEPFET Collaboration

RD11, 6-8 July 2011 Florence



# Belle II DEPFET pixel detector

- Vertex detector layout for SuperKEKB
  - Challenges and requirements
- Overview of Belle-II PXD
  - DEPFET module concept
  - Mechanics and cooling
  - Front- end and PXD DAQ
- Results from test systems



**Upgrade of B factory KEKB**

**SuperKEKB goal luminosity:**

$$\mathcal{L} = 8 \times 10^{35} \text{ cm}^{-2} \text{ s}^{-1}$$

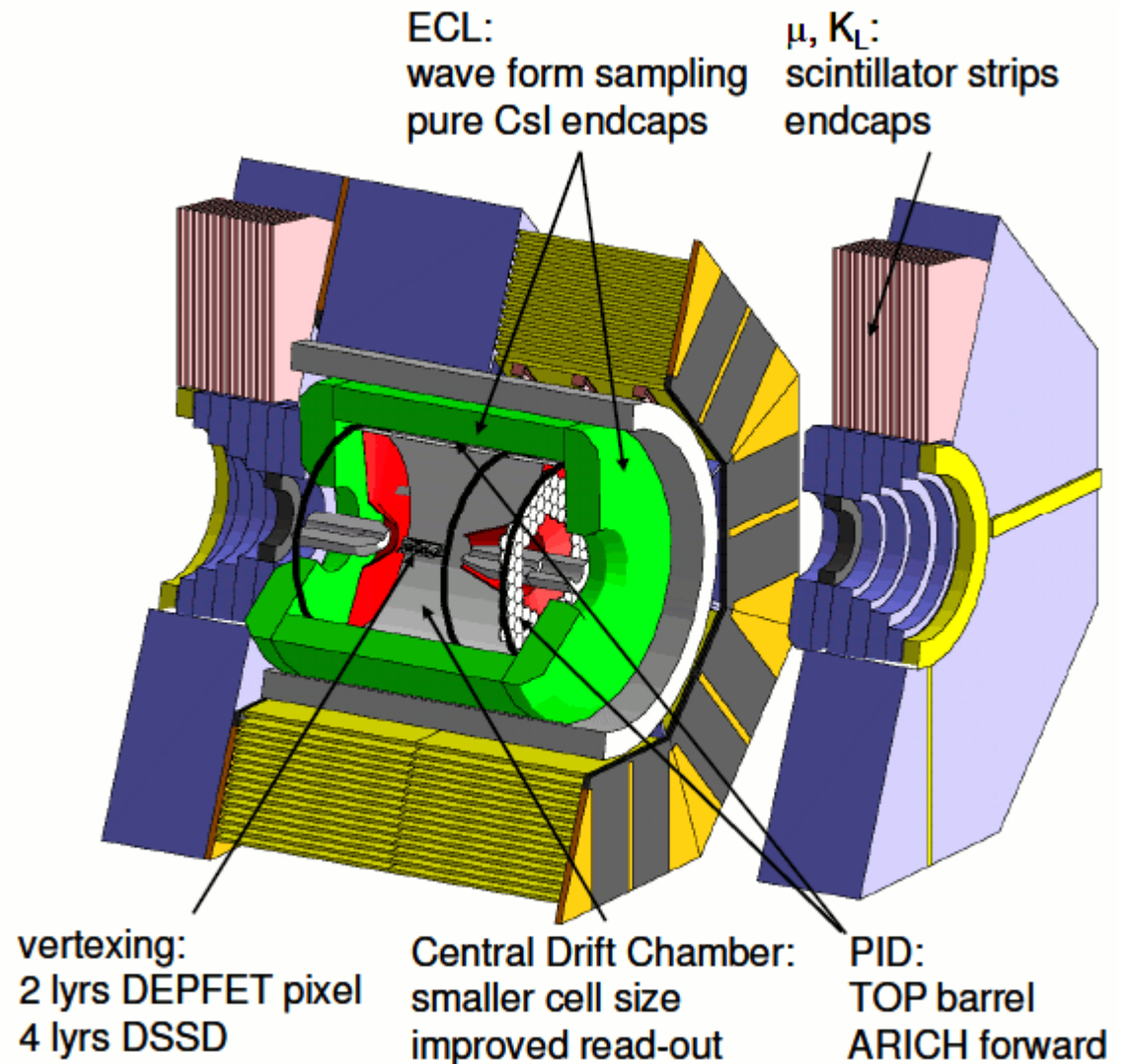
# SuperKEKB and Belle II

Luminosity upgrade realized with Nano Beam option

- Larger crossing angle: 22mrad  $\rightarrow$  83mrad
- Smaller asymmetry LER/HER: 3.5/8GeV  $\rightarrow$  4/7GeV
- Squeeze beta functions ( $/20$ )
- Increase beam currents ( $\times 2$ )

Have to deal with

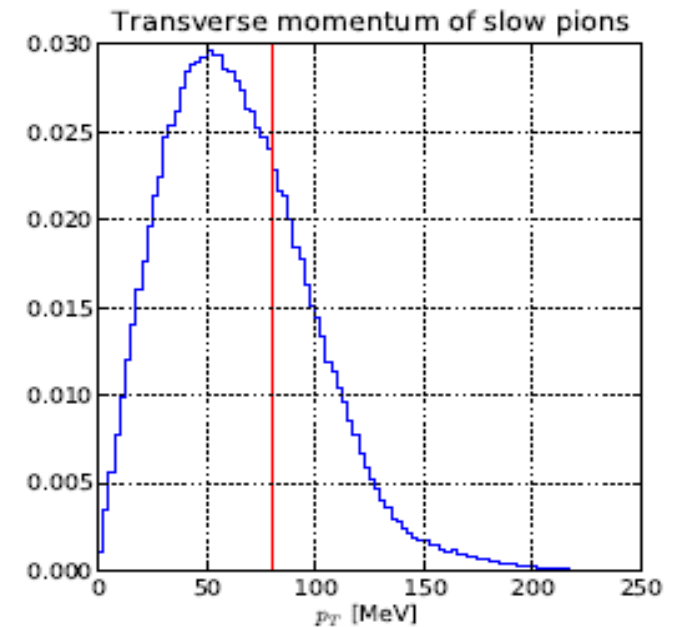
- Harsh radiation environment: 1MRad/year
- Higher density of background hits ( $\times 30$  Touchek effect)
- L1 trigger rate  $\sim 30$ kHz



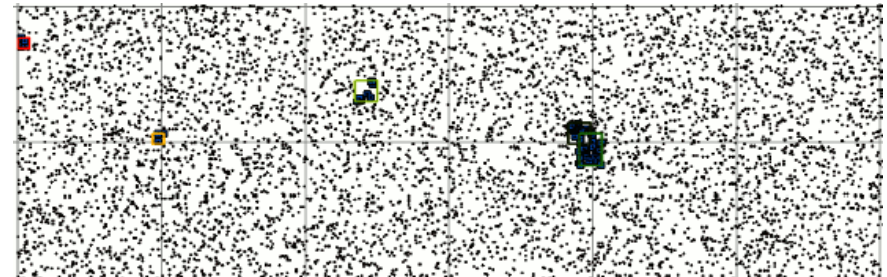
# Vertex Detector Goals

- Improved vertex resolution for Belle II
  - DEPFET layers closest to IP
  - Single point resolution  $\sim 10\mu\text{m}$
- Low material budget of  $0.2\% X_0$  per ladder
  - All silicon ladders, thinned sensors
- Max. acceptable pixel occupancy  $< 3\%$ 
  - Small pixels and parallelized readout
- High hit efficiency down to  $p_T \sim 50\text{MeV}$
- Data reduction to  $\sim 100\text{kB/event}$  at  $\sim 6\text{kHz}$
- Very little space between beam pipe and SVD
  - Integrated cooling
- Sufficient radiation hardness Sensor/ASICs
  - See talk by A. Ritter

$$D^{*+/-} \rightarrow D^0 \pi^{+/-}$$



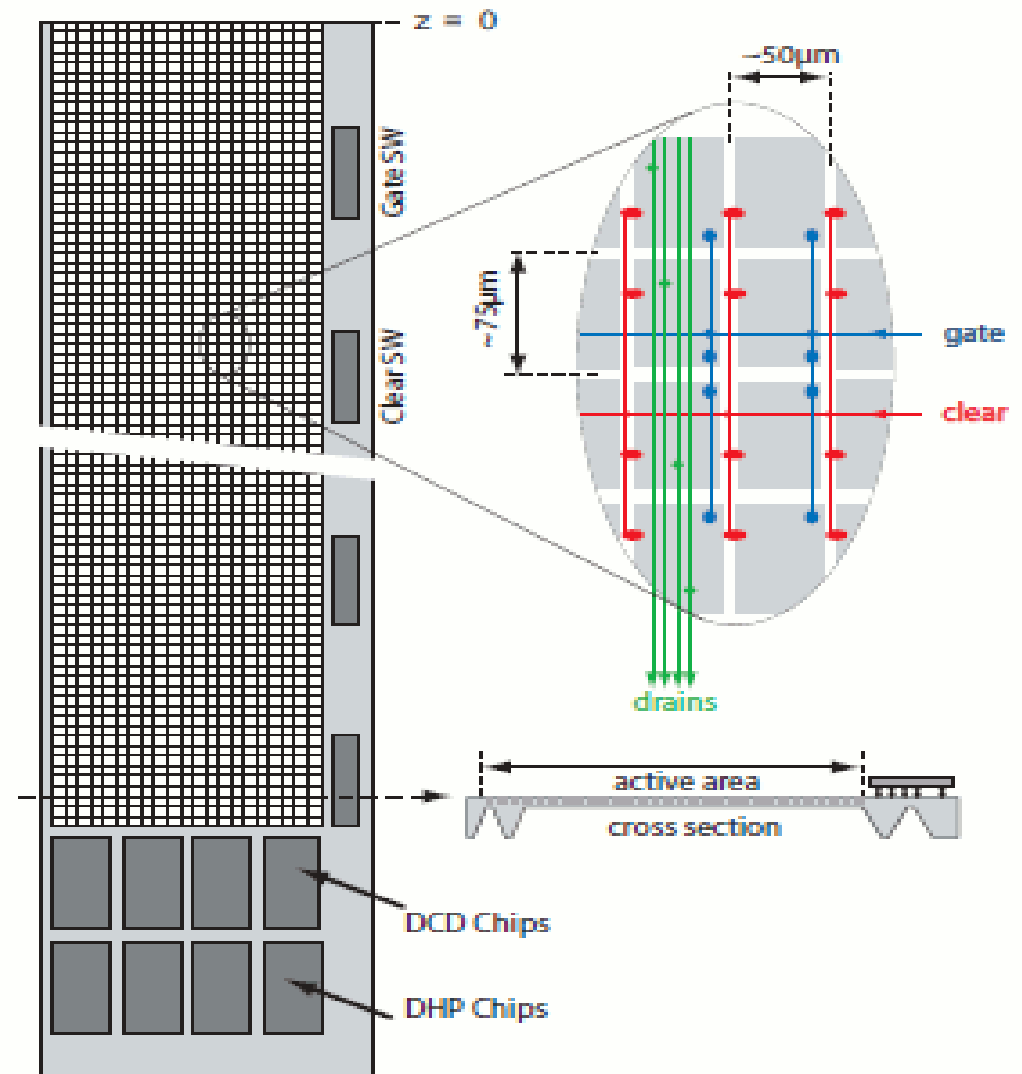
**Module with 3% occupancy**



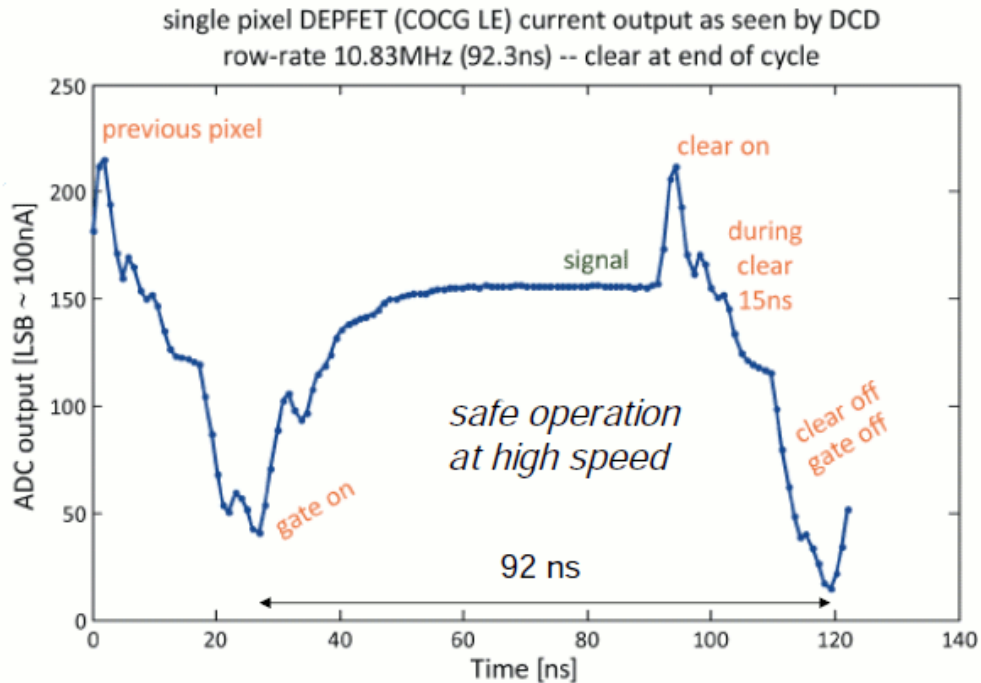


# Module Concept

- All silicon module
  - Directly bonded support frame
  - All ASICs bump bonded
  - 3 Metal layers for circuitry
- Front- end ASICS
  - Switcher-B: controls DEPFET gate and clear lines.
  - DCD-B: multichannel ADC chips; Digitizes drain currents.
  - DHP: digital processor chips; 0-supression & triggered readout
- Rolling shutter readout
  - Read signals row-by-row
  - 4 rows in parallel



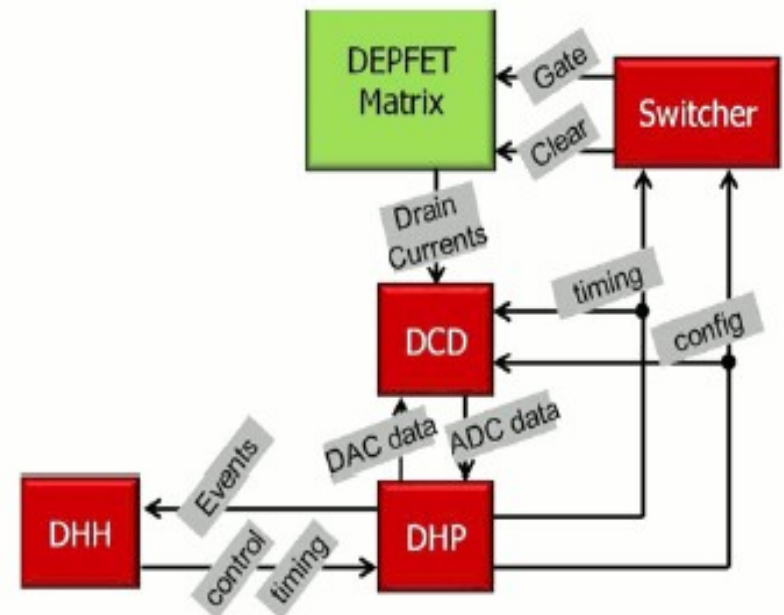
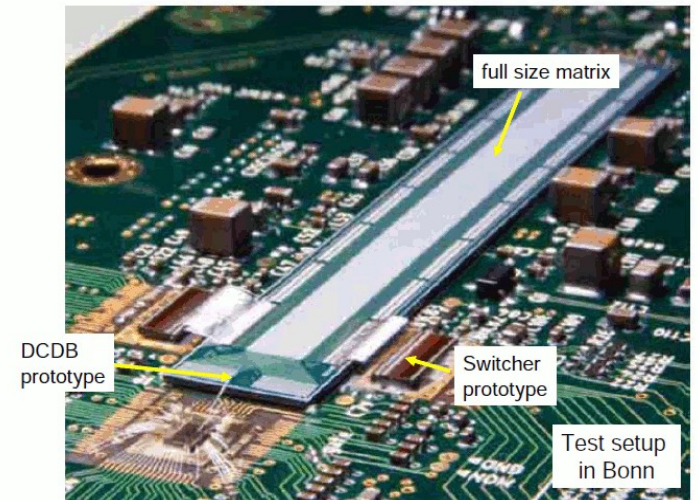
# Readout Timing



Full speed readout demonstrated

DEPFET PXD readout time is 20us

- Read-Clear cycle in ~100ns
- PXD integrates ~5000 bunch crossings
- 50KHz (Frame rate) vs. 30kHz (L1 Trigger)



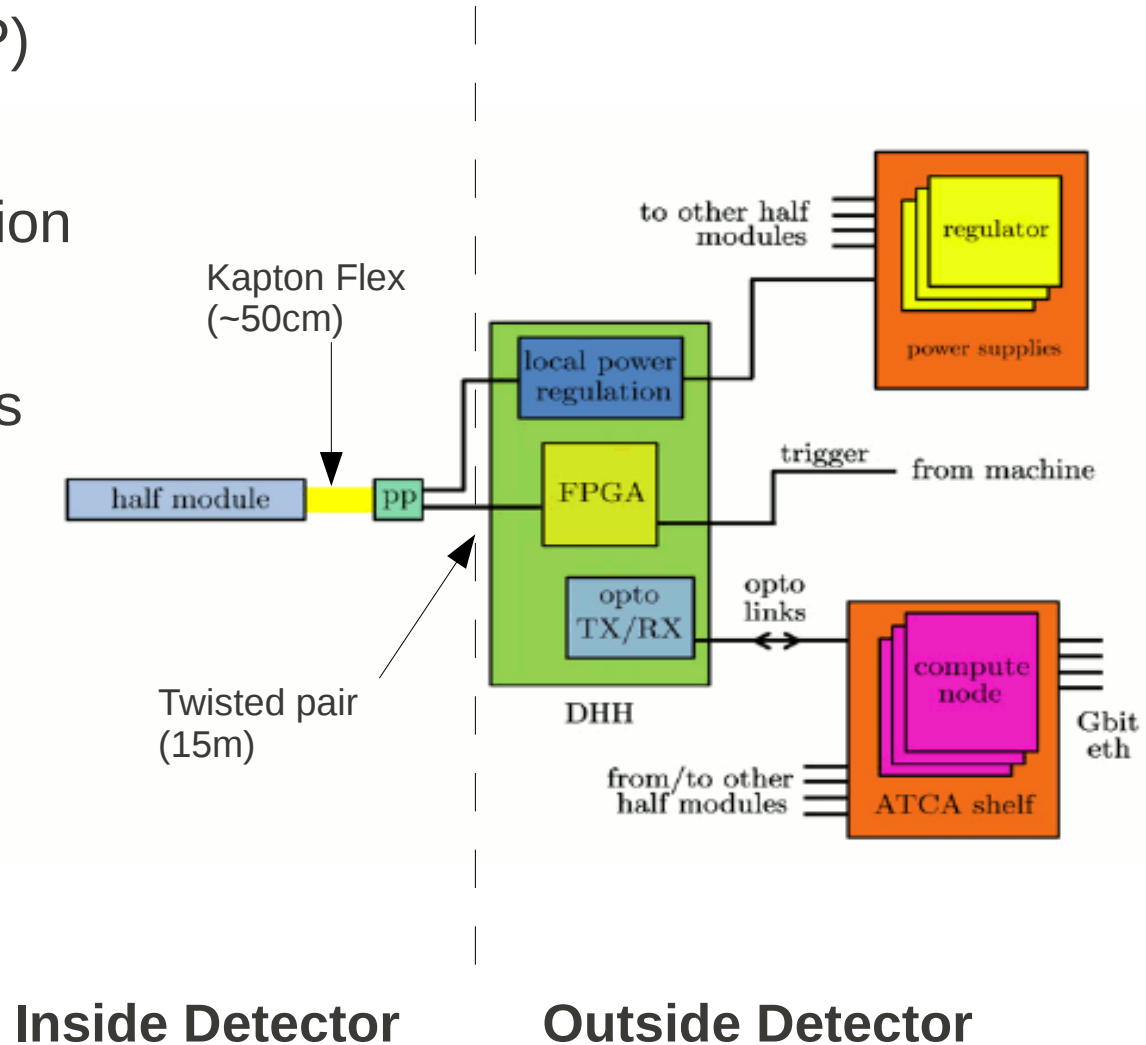
# Readout Chain

## Passive patch panel (PP)

- High radiation area
- Over-voltage protection
- Sense wires

## Total of 40 DHH modules

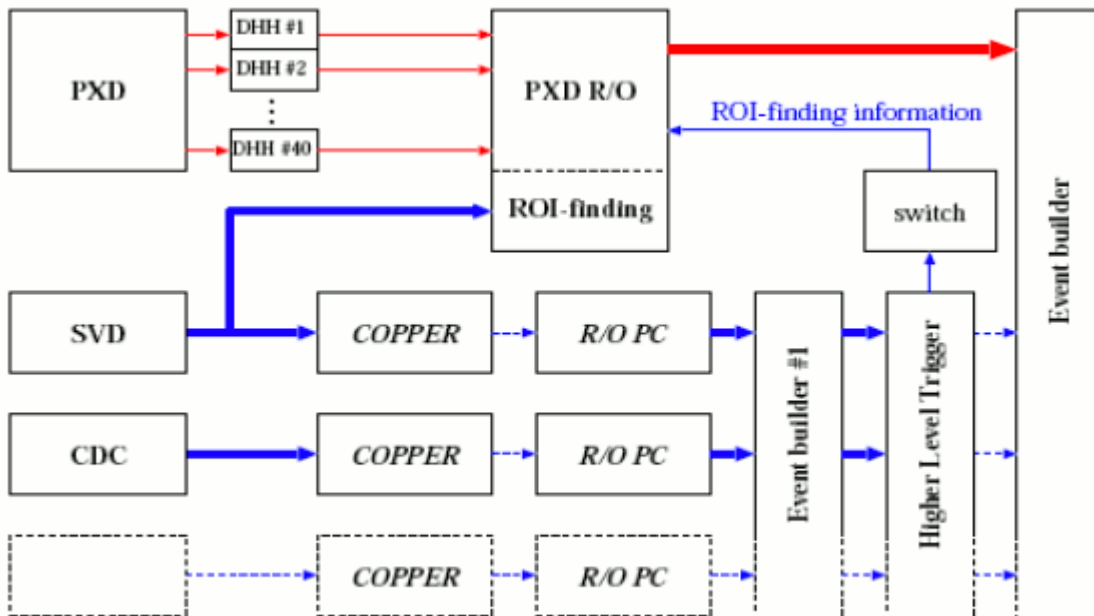
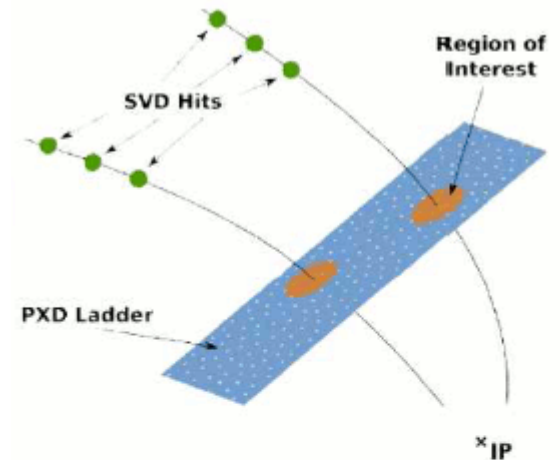
- Easy access
- Commercial FPGA's





# PXD DAQ Layout

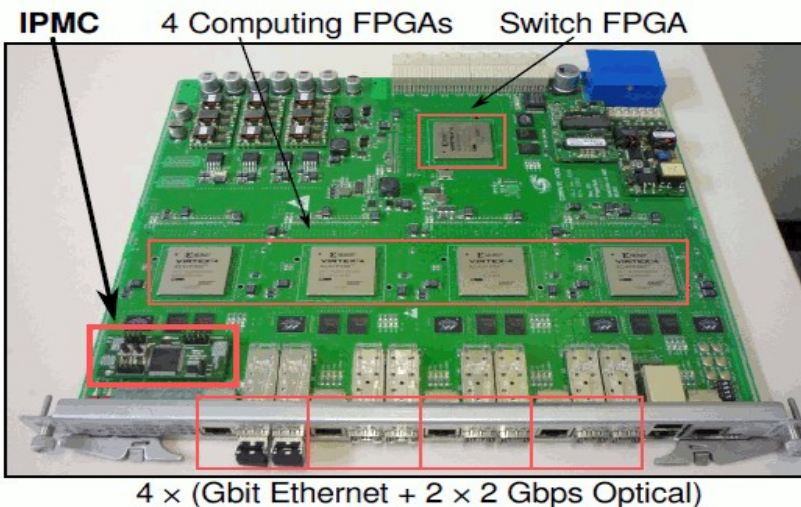
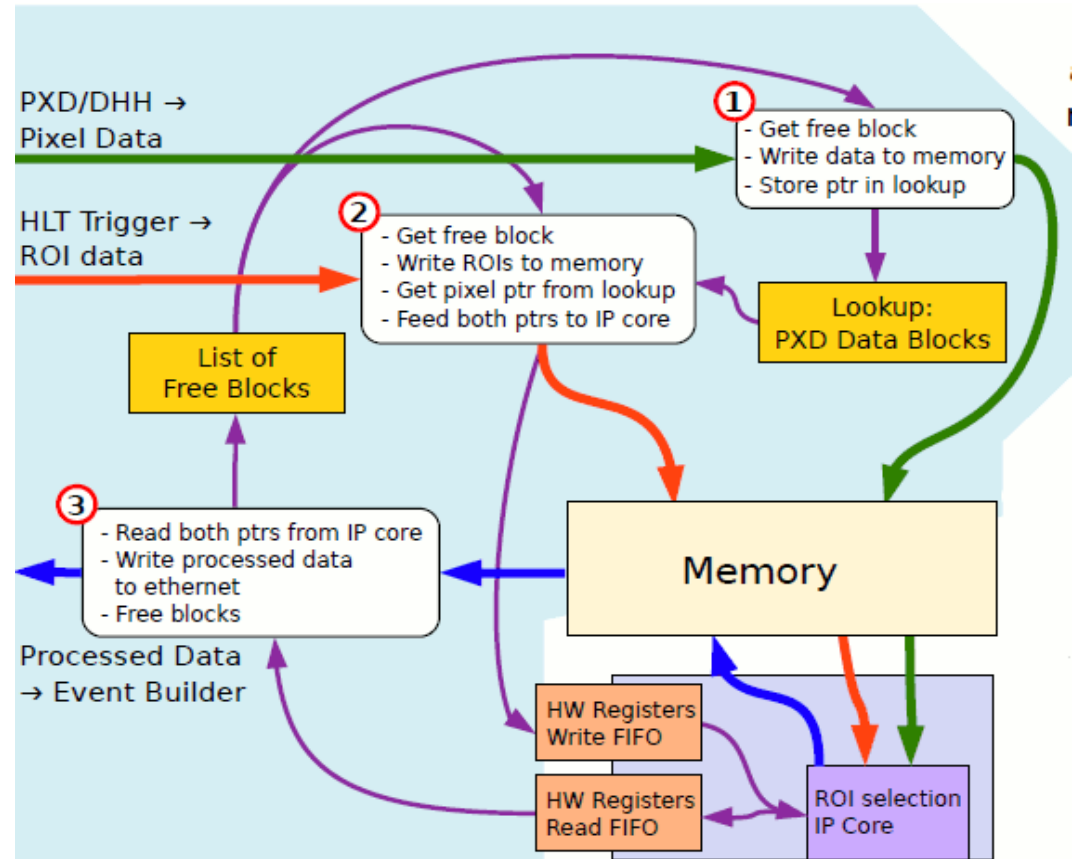
- PXD sends ~1MB/event at rate ~30kHz to PXD DAQ
- Required size reduction /10 using SVD (+CDC) tracks
- Required rate reduction /5 using HLT tag



Noise reduction by track association: Only pixels inside the ROI will be stored (+ high energy deposition clusters)

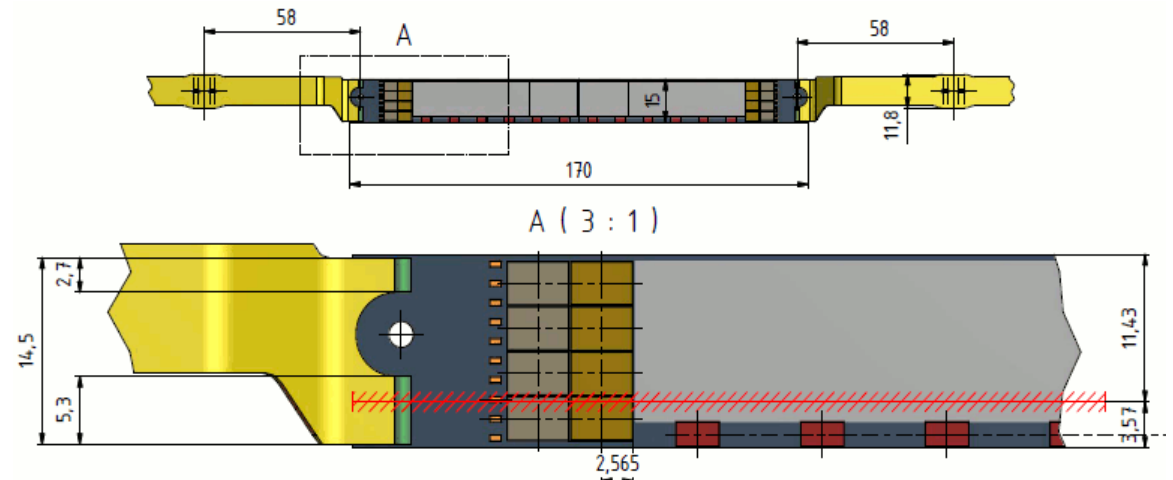
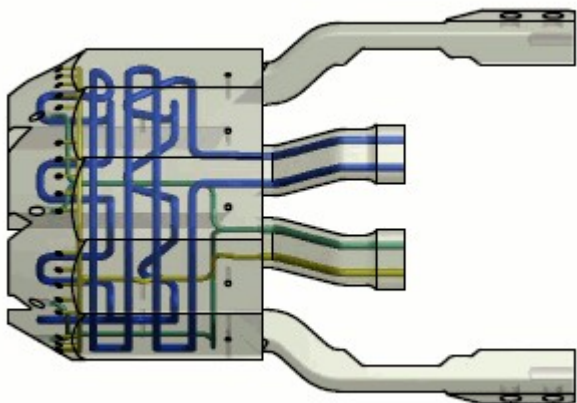
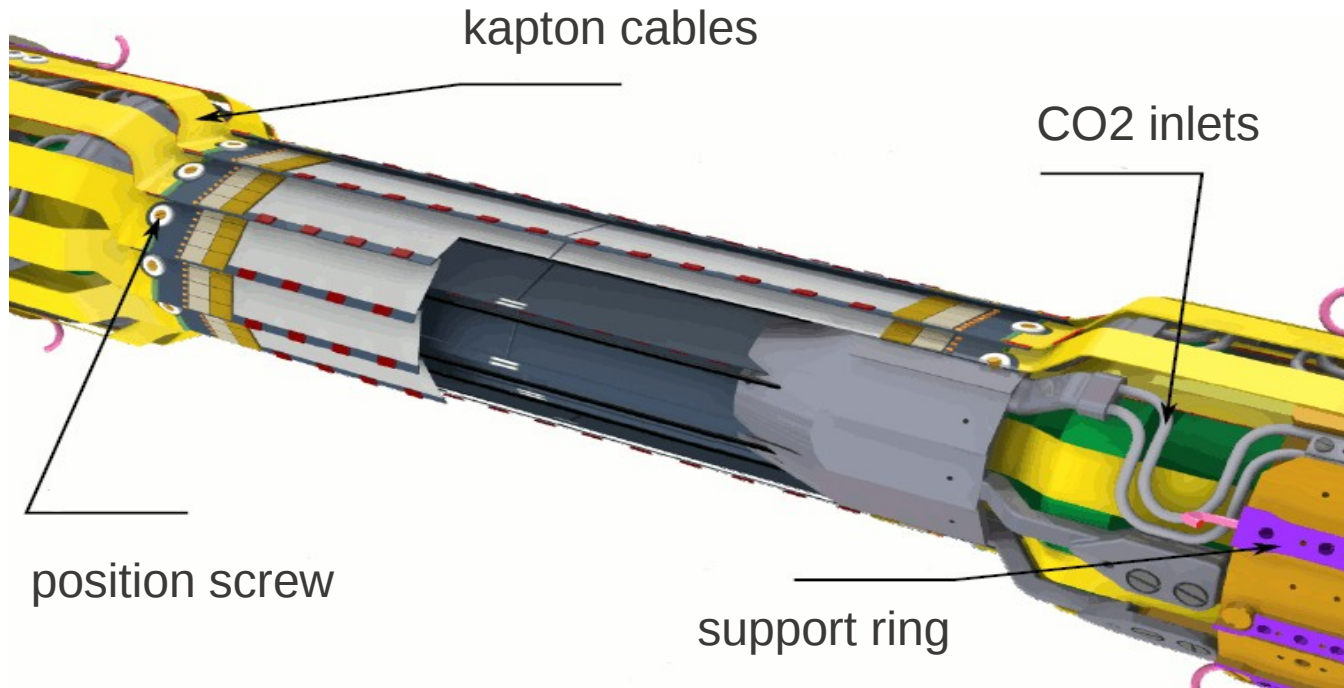
# PXD DAQ: ATCA System

- Shelf with ~10 Compute Nodes
- Gbit Ethernet/FPGA
- 2 x 6.25 Gbps optical/FPGA
- 4 x 4GB DDR2 RAM memory
- Achieved 380MB/s read and 360MB/s write

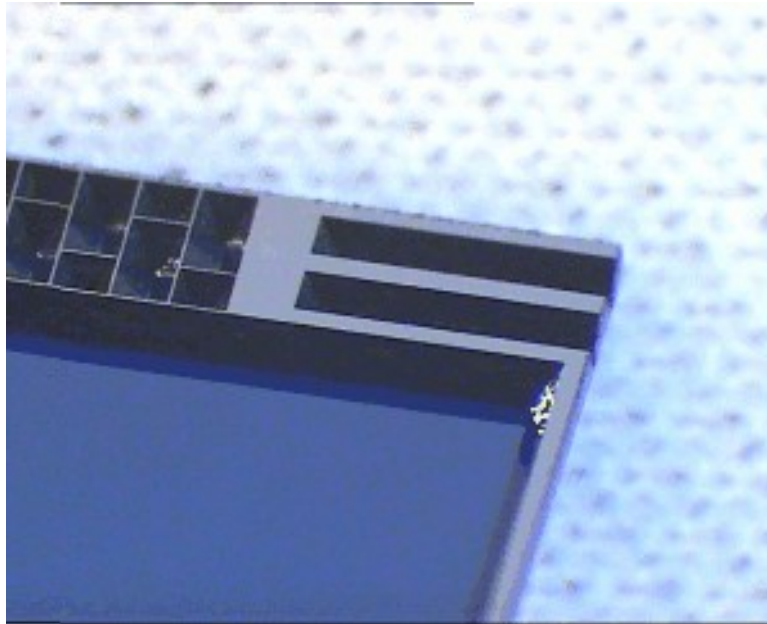


Highly Parallized ROI algorithm:  
:- 4 IP core / FPGA  
:- 31 ROI's / core

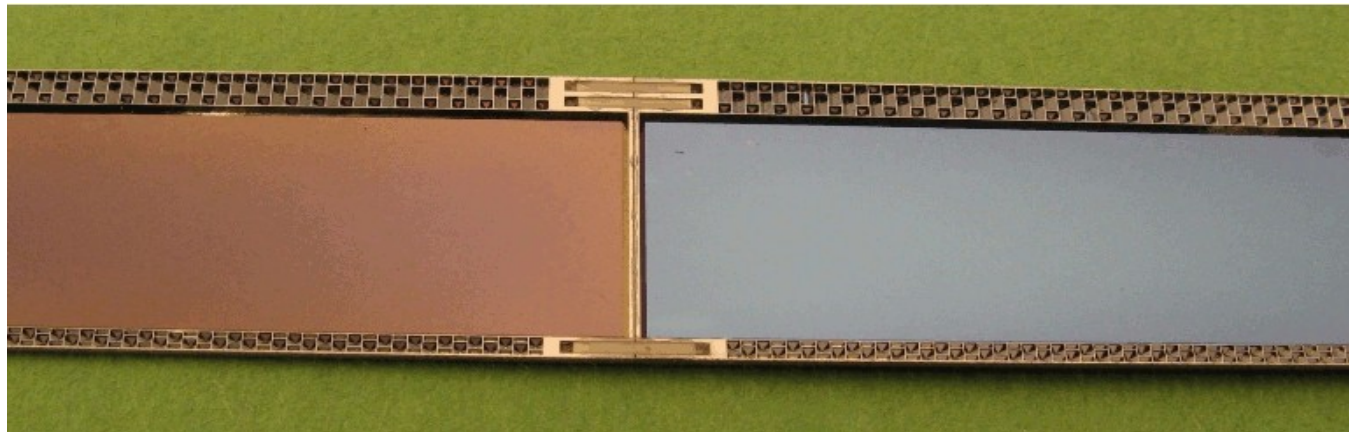
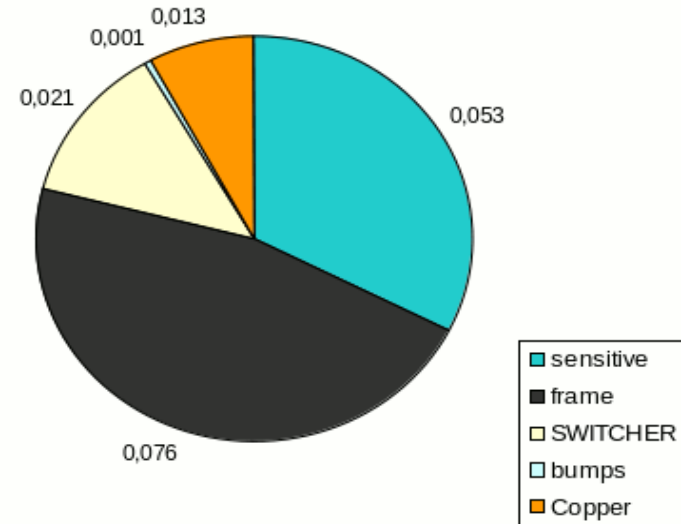
# Mechanical Design



# Thinning & Material Budget



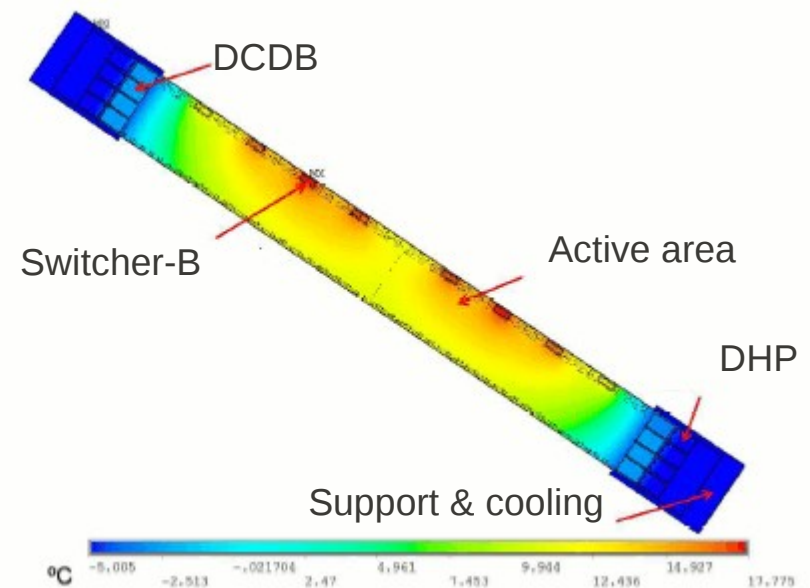
TDR: 0.164 %X0 (50  $\mu\text{m}$  top, 450  $\mu\text{m}$  frame)



# Thermal Environment

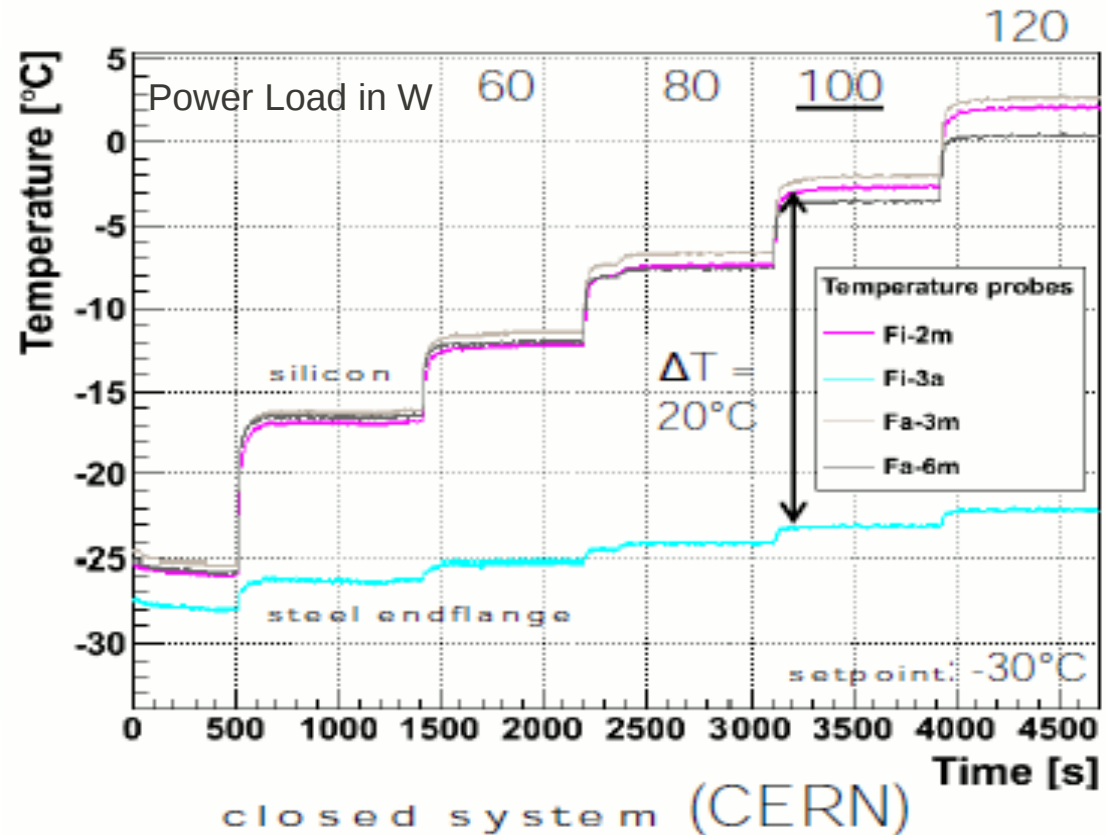
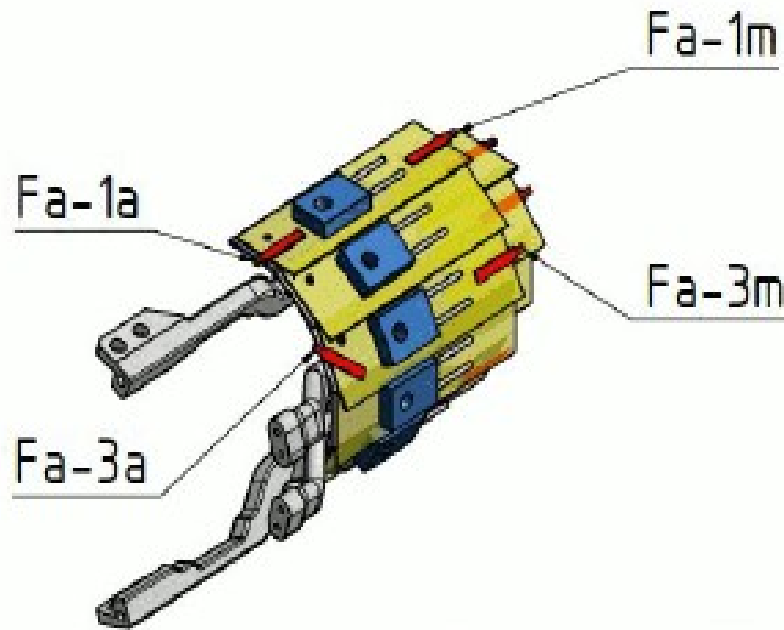
- Total heat load of 360W = 40 x 9W
  - 0.5W switchers
  - 0.5W DEPFET pixels
  - 6W DCD's && 2W DHP's
- DEPFET's < 30°C
  - Limit leakage currents
  - uniform response
- ASIC's < 60°C
- End of stave cooled by conducti
  - evaporative CO2 cooling
- Inner module cooled by convection
  - cold dry air blown at Switcher-B

## Thermal Simulations



**Now, cooling tests ->**

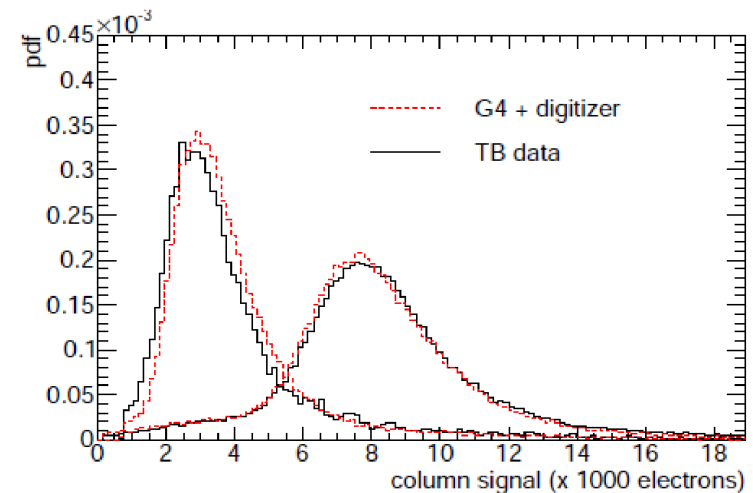
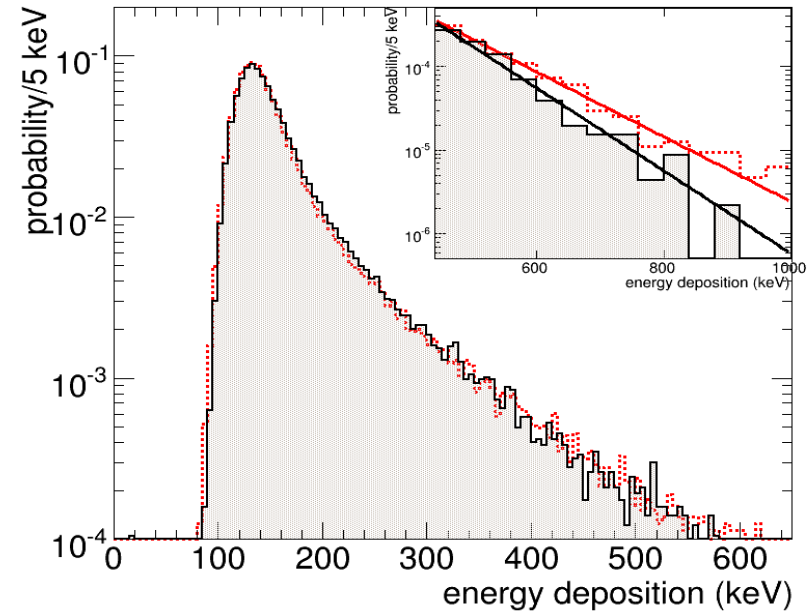
# CO2 Cooling Test Setups



- CO2 cooling works with closed CO2 system @ CERN
- Common CO2 cooling system PXD + SVD in progress

# DEPFET Test Systems

- Tests of DEPFET prototype devices
- Validation of fast DEPFET simulation
- Response to minimum ionizing particles @ CERN SPS:
  - Use most probable signal to extract  $g_q = \Delta I_D / Q$
  - $6\mu\text{m}$  gate length  $\rightarrow \sim 300\text{pA/e-}$
  - $5\mu\text{m}$  gate length  $\rightarrow \sim 650\text{pA/e-}$
  - Resolution  $\sim 1\mu\text{m}$  @  $20 \times 20\mu\text{m}^2$  pitch and  $450\mu\text{m}$  thick.
- New prototypes thinned down to  $50\mu\text{m}$  thickness tested



# In Summary: Recent Achievements

- Prototype system with DEPFET (50um) DCDB and SWB operated in lab measurements:
  - Sample-Clear cycle in 100ns → full speed!!
  - S/N ~20 → goal is S/N ~20-40
- CO2 cooling of endflange with open CO2 system demonstrated and working.
- ATCA based PXD DAQ system is operational
- First combined simulation of backgrounds (QED, radiative bhabba, Touchek)
  - Occupancy in 1<sup>st</sup> layer < 1% → PXD DAQ can handle 3%

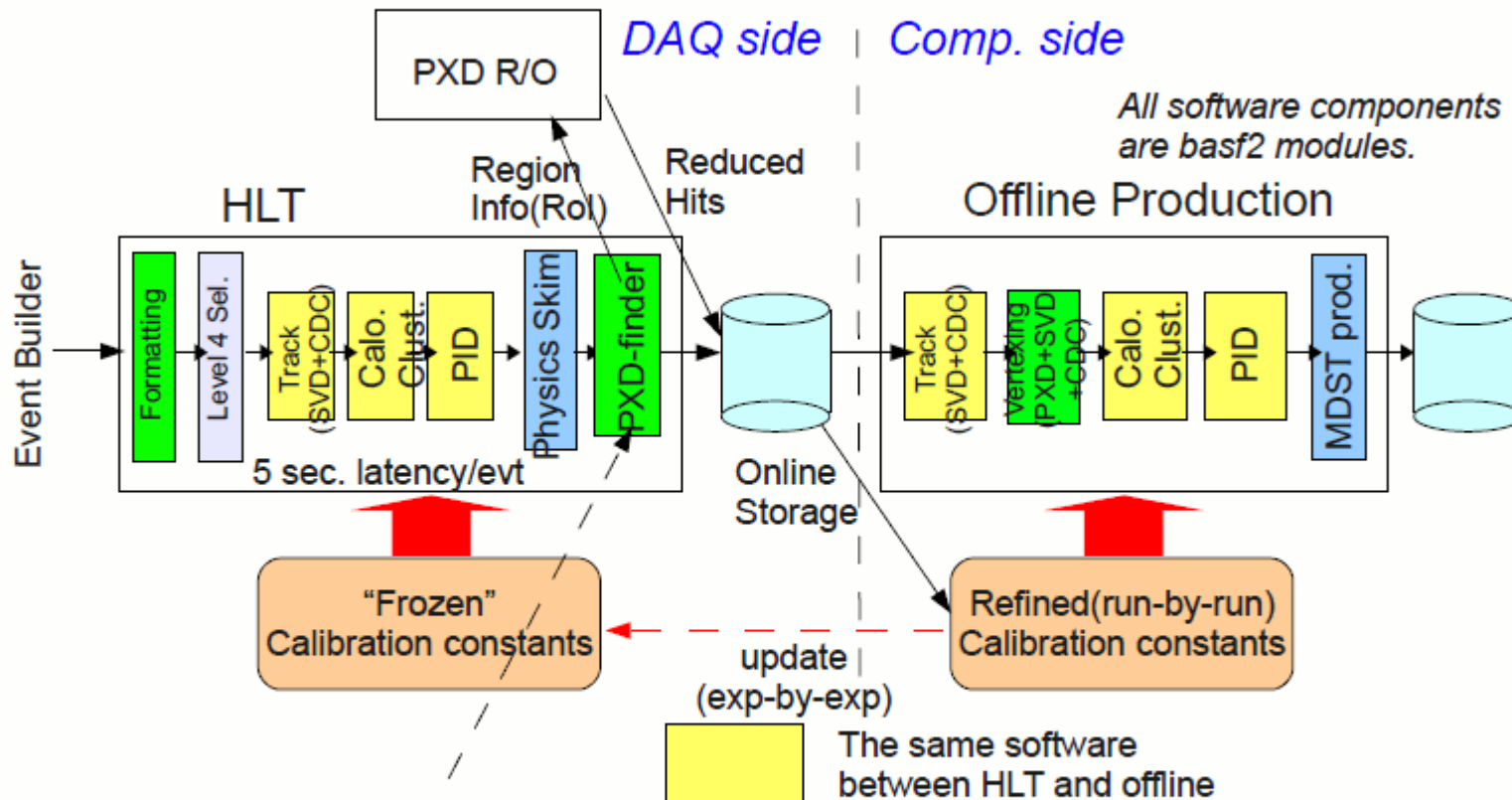
**First collision data expected 2014; PXD in detector in 2015**



Thank you for your attention

Backup Slides

# HLT Event Processing chain

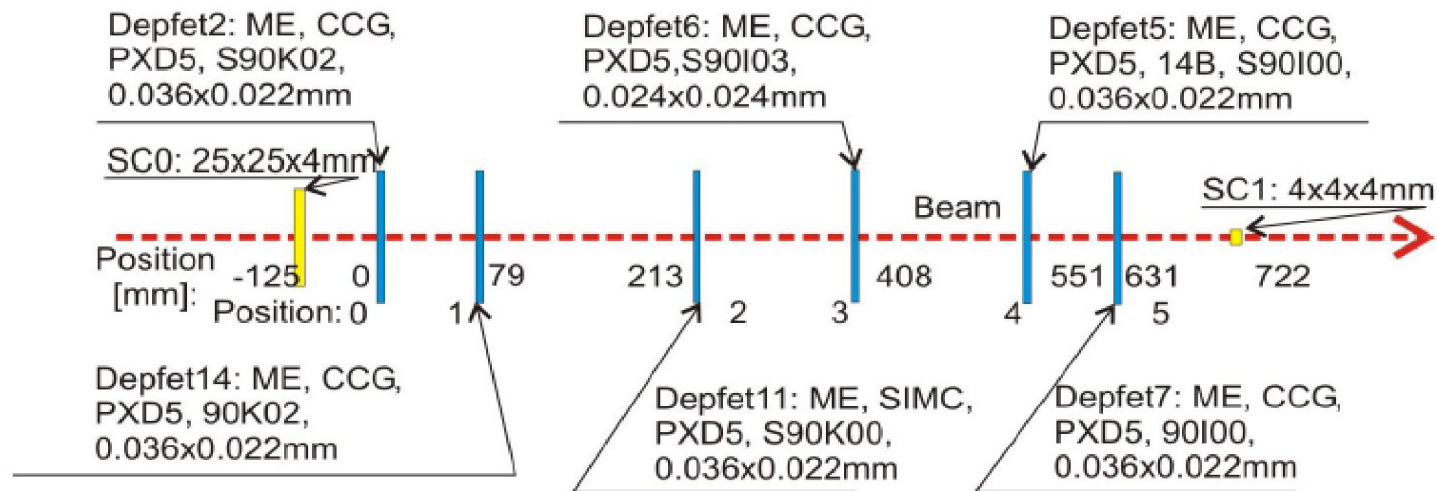


**Special track finder for track-PXD hit association**

- \* Only for the HLT-triggered events
- \* Can make use of SVD+CDC raw data + full tracking results also

*already parallel processing with 2000 cores @ 3GHz*

# DEPFET test beam campaigns



- Data from DEPFET test beams with 120GeV pions at CERN SPS collected in 2008/2009.
- DEPFET only telescope: ILC type DEPFET's with 128x64 or 256x64 pixels.
- Non zero suppressed analog readout at slow rate of  $\sim 2\mu\text{s}$  per frame with S3A/S3B boards.
- Systematic studies for DEPFET characterization:
  - High statistics and low occupancy scans  $\rightarrow$  point resolution
  - Scan of DUT incidence angle
  - Scan of beam energy (down to 40GeV)
  - Scan of DEPFET backplane voltage ...